

# TJ20A10M3

## Switching Regulator Applications

- Low drain-source ON resistance:  $R_{DS(ON)} = 63 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 50 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = -10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = -100 \text{ V}$ )
- Enhancement-model:  $V_{th} = -2.0$  to  $-4.0 \text{ V}$  ( $V_{DS} = -10 \text{ V}$ ,  $I_D = -1 \text{ mA}$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

| Characteristics                                      |                | Symbol    | Rating     | Unit             |
|------------------------------------------------------|----------------|-----------|------------|------------------|
| Drain-source voltage                                 |                | $V_{DSS}$ | -100       | V                |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ ) |                | $V_{DGR}$ | -100       | V                |
| Gate-source voltage                                  |                | $V_{GSS}$ | $\pm 20$   | V                |
| Drain current                                        | DC (Note 1)    | $I_D$     | -20        | A                |
|                                                      | Pulse (Note 1) | $I_{DP}$  | -40        |                  |
| Drain power dissipation ( $T_c = 25^\circ\text{C}$ ) |                | $P_D$     | 35         | W                |
| Single pulse avalanche energy (Note 2)               |                | $E_{AS}$  | 124        | mJ               |
| Avalanche current                                    |                | $I_{AR}$  | -20        | A                |
| Repetitive avalanche energy (Note 3)                 |                | $E_{AR}$  | 2.29       | mJ               |
| Channel temperature                                  |                | $T_{ch}$  | 150        | $^\circ\text{C}$ |
| Storage temperature range                            |                | $T_{stg}$ | -55 to 150 | $^\circ\text{C}$ |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Please use devices on condition that the channel temperature is below  $150^\circ\text{C}$ .

Note 2:  $V_{DD} = -25 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$ ,  $L = 500 \text{ }\mu\text{H}$ ,  $R_G = 25 \text{ }\Omega$ ,  $I_{AR} = -20 \text{ A}$

Note 3: Repetitive rating; pulse width limited by maximum channel temperature.

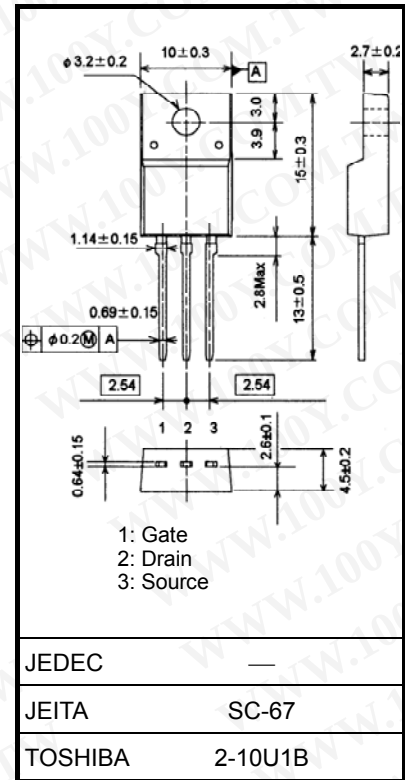
## Thermal Characteristics

| Characteristics                        | Symbol         | Max  | Unit                        |
|----------------------------------------|----------------|------|-----------------------------|
| Thermal resistance, channel to case    | $R_{th(ch-c)}$ | 3.57 | $^\circ\text{C} / \text{W}$ |
| Thermal resistance, channel to ambient | $R_{th(ch-a)}$ | 62.5 | $^\circ\text{C} / \text{W}$ |

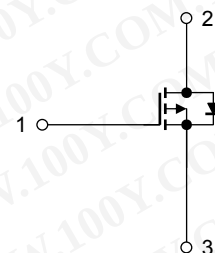
This transistor is an electrostatic sensitive device. Please handle with caution.

勝特力材料 886-3-5753170  
 勝特力电子(上海) 86-21-34970699  
 勝特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

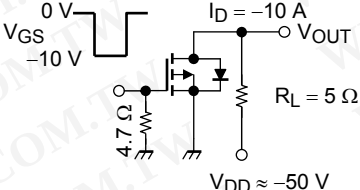
Unit: mm



Weight: 1.7 g (typ.)



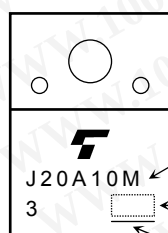
## Electrical Characteristics (Ta = 25°C)

| Characteristics                                 |               | Symbol               | Test Condition                                                                                                          | Min  | Typ. | Max  | Unit |
|-------------------------------------------------|---------------|----------------------|-------------------------------------------------------------------------------------------------------------------------|------|------|------|------|
| Gate leakage current                            |               | I <sub>GSS</sub>     | V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V                                                                          | —    | —    | ±100 | nA   |
| Drain cut-OFF current                           |               | I <sub>DSS</sub>     | V <sub>DS</sub> = -100 V, V <sub>GS</sub> = 0 V                                                                         | —    | —    | -10  | μA   |
| Drain-source breakdown voltage                  |               | V (BR) DSS           | I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V                                                                          | -100 | —    | —    | V    |
|                                                 |               | V (BR) DSX           | I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 20 V                                                                         | -75  | —    | —    |      |
| Gate threshold voltage                          |               | V <sub>th</sub>      | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA                                                                         | -2.0 | —    | -4.0 | V    |
| Drain-source ON resistance                      |               | R <sub>DS (ON)</sub> | V <sub>GS</sub> = -10 V, I <sub>D</sub> = -10 A                                                                         | —    | 63   | 90   | mΩ   |
| Forward transfer admittance                     |               | Y <sub>fs</sub>      | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -10 A                                                                         | 25   | 50   | —    | S    |
| Input capacitance                               |               | C <sub>iSS</sub>     | V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0 V, f = 1 MHz                                                                | —    | 5500 | —    | pF   |
| Reverse transfer capacitance                    |               | C <sub>rSS</sub>     |                                                                                                                         | —    | 200  | —    |      |
| Output capacitance                              |               | C <sub>oSS</sub>     |                                                                                                                         | —    | 290  | —    |      |
| Switching time                                  | Rise time     | t <sub>r</sub>       | <br>Duty ≤ 1%, t <sub>w</sub> = 10 μs | —    | 13   | —    | ns   |
|                                                 | Turn-on time  | t <sub>on</sub>      |                                                                                                                         | —    | 27   | —    |      |
|                                                 | Fall time     | t <sub>f</sub>       |                                                                                                                         | —    | 105  | —    |      |
|                                                 | Turn-off time | t <sub>off</sub>     |                                                                                                                         | —    | 420  | —    |      |
| Total gate charge (gate-source plus gate-drain) |               | Q <sub>g</sub>       | V <sub>DD</sub> ≈ -80 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -20 A                                                | —    | 120  | —    | nC   |
| Gate-source charge                              |               | Q <sub>gs</sub>      |                                                                                                                         | —    | 20   | —    |      |
| Gate-drain ("miller") charge                    |               | Q <sub>gd</sub>      |                                                                                                                         | —    | 32   | —    |      |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol           | Test Condition                                  | Min | Typ. | Max | Unit |
|-------------------------------------------|------------------|-------------------------------------------------|-----|------|-----|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub>  | —                                               | —   | —    | -20 | A    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | —                                               | —   | —    | -40 | A    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | I <sub>DR</sub> = -20 A, V <sub>GS</sub> = 0 V  | —   | —    | 1.4 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | I <sub>DR</sub> = -20 A, V <sub>GS</sub> = 0 V, | —   | 76   | —   | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>  | dI <sub>DR</sub> /dt = -50 A/μs                 | —   | 104  | —   | nC   |

## Marking



Part No.  
(or abbreviation code)

Lot No.

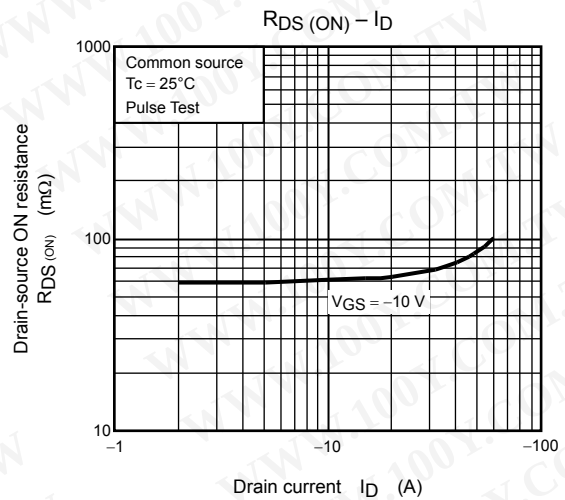
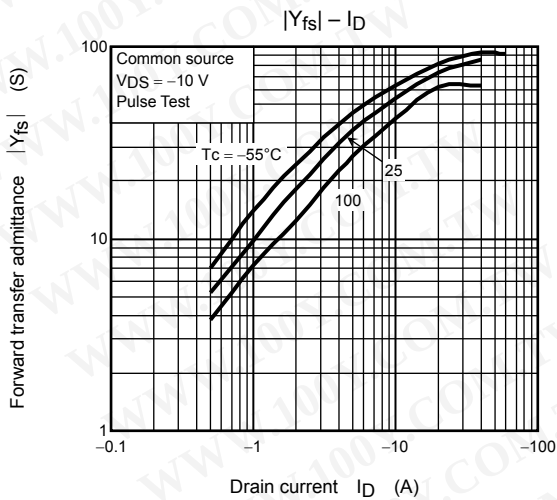
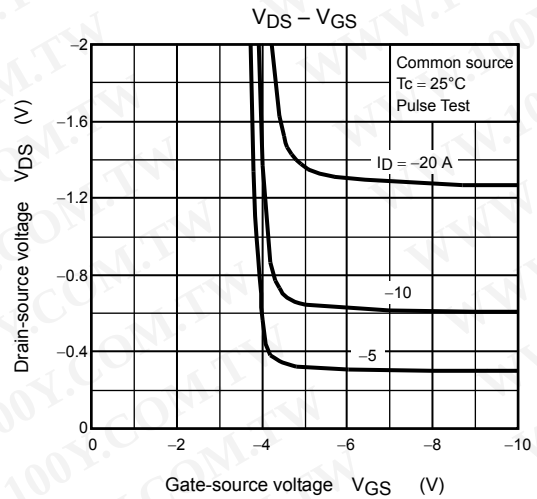
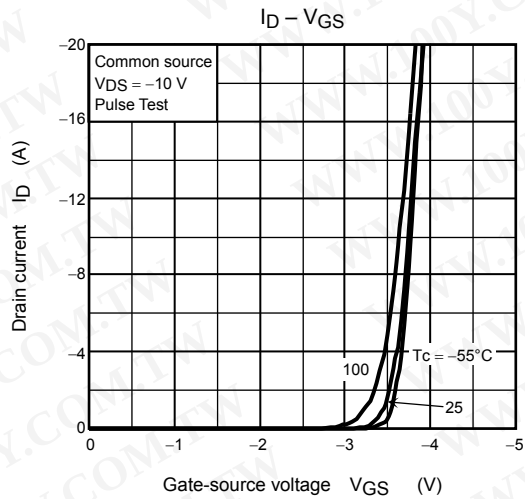
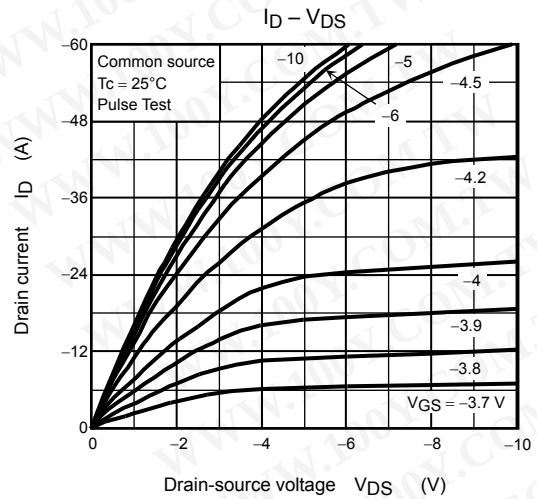
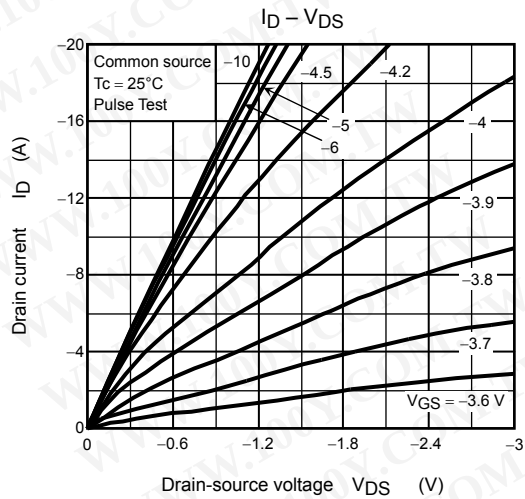
Note 4

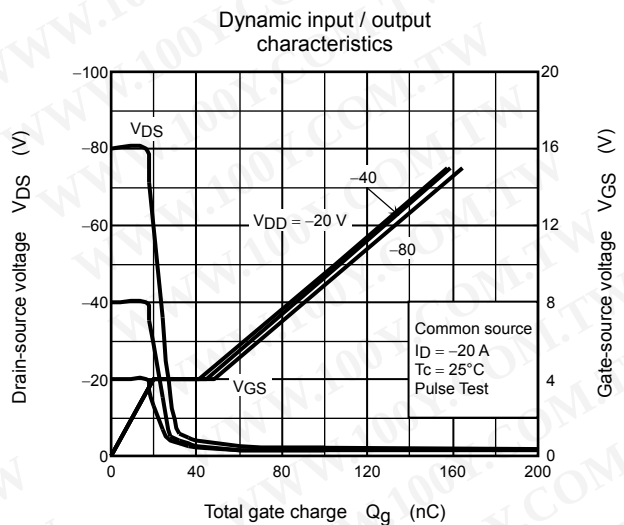
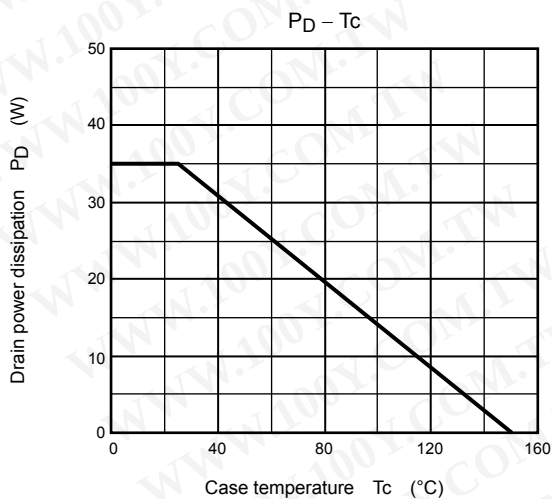
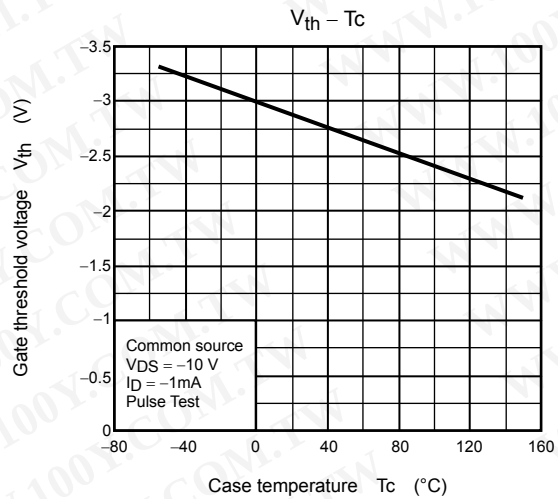
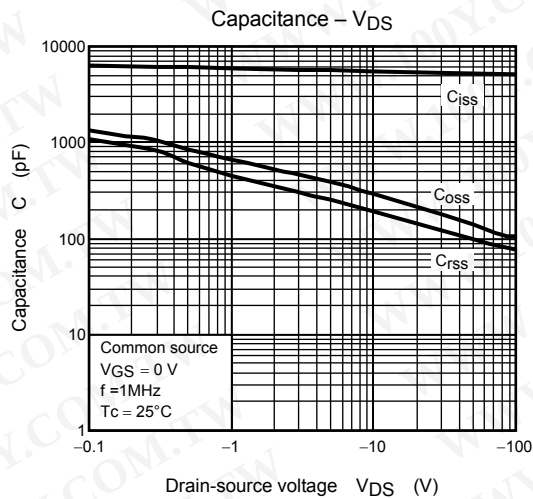
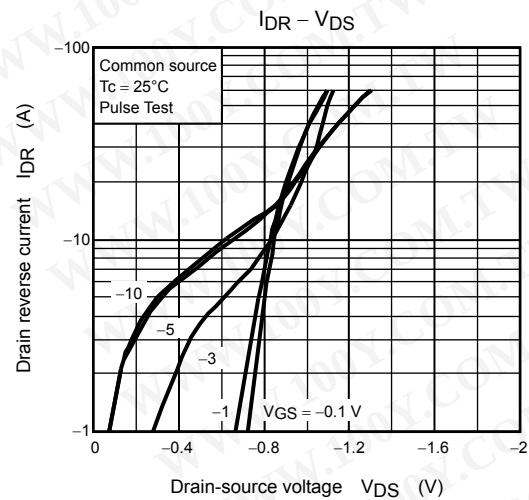
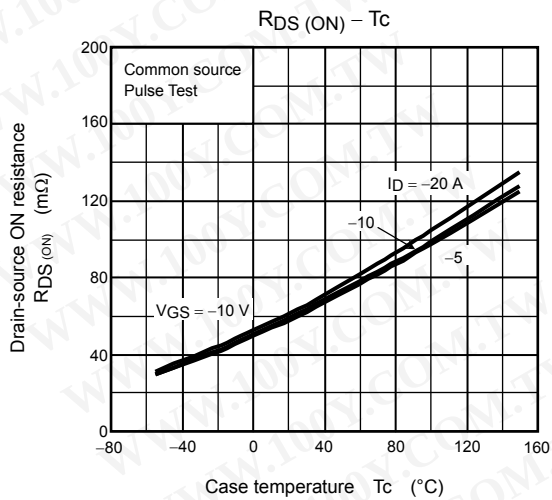
Note 4: A line under a Lot No. identifies the indication of product Labels

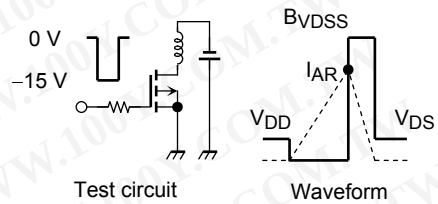
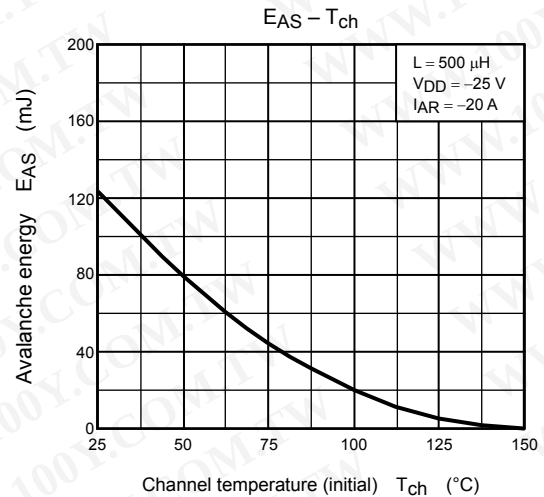
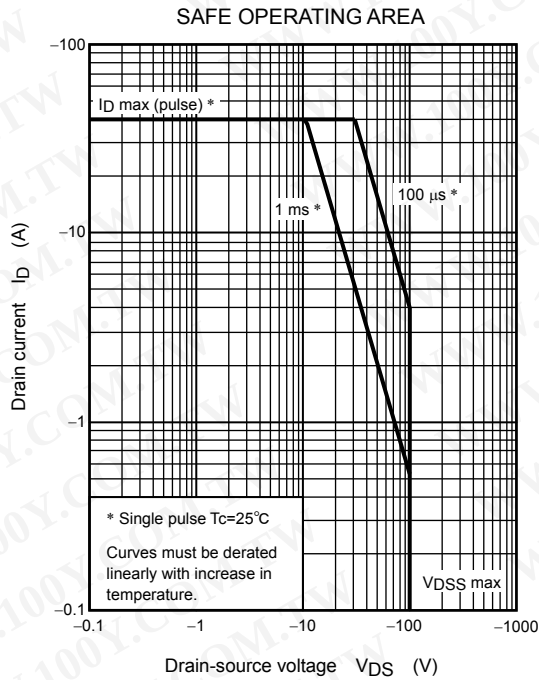
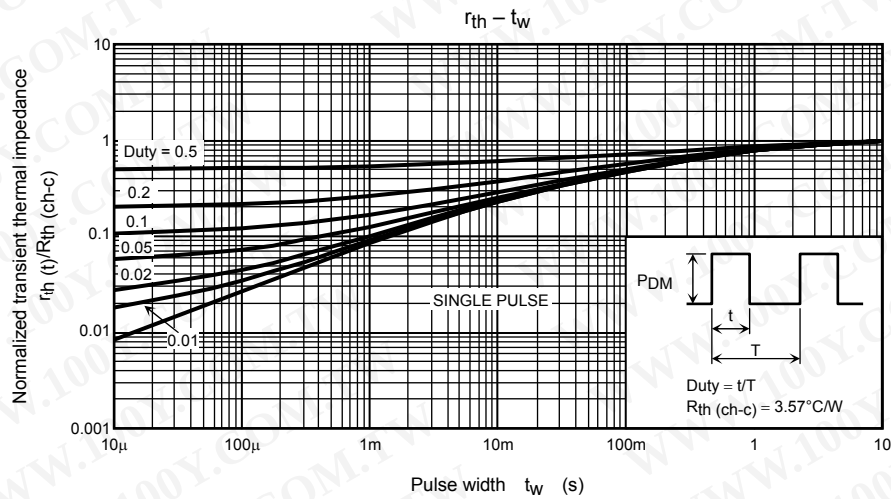
Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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$$R_G = 25 \Omega$$

$$V_{DD} = -25 V, L = 500 \mu H$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{B_{V_{DS}}}{B_{V_{DS}} - V_{DD}} \right)$$

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